

## **REVOCATION AND POWER OF ATTORNEY**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 Feb 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

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Schedule A					
App # 2.3	Title	: ∠inventor(s)	Filing Date	New Attorney & Docket No.	Former/Attorney
	Compositions for Cleaning Organic and Plasma Etched Residues for				
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
00/07/ 000	Method of and Apparatus for		00/00/0004		
09/874,330	Substrate Pre-Treatment Chemical Mechanical Polishing	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
	Oxalic Acid as a Semiaqueous		<del> </del>		
	Cleaning Product for Copper and				
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/193,185	Sulfoxide Pyrolid(in)one Alkanolamine Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
10/100/100		aniou, or an	0111212002	00001 110 00	0317-110-333
	Method for the Deposition of Materials		•		
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
10/007,134	Post Etch Cleaning Composition for Dual Damascene System	Payro et al	12/04/2001	60027 422 116	9347 433 000
10/007,134	Photolytic Conversion Process to	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
09/988,545	Having Reduction and Oxidation  Potential	Loo et al	11/20/2001	60027 407 140	0247 407 000
09/900,040	Method and Compositions for	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Chemically Treating A Substrate				
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including Nucleophilic Amine Compound				
40405.005	Having Reduction and Oxidation		0.7/0.//0.000		
10/135,695	Potential Fluoride Layer and Removing Same	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/446,127	Process for the Use of Bis-Choline	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	and Tris-Choline in the Cleaning of				
	Quartz-Coated Polysilicon and Other				
10/689,657	Materials Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
	Cleaning Compositions Containing		,		
	Hydroxylamine Derivatives and		•		
10/689,620	Process Using Same for Residue Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
		2.754, 51 4.7		140 00	3311 140-333
	Composition for Exfoliation Agent to				
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using Fluoride Chemistries to Remove Post-	!			
	Etch Residues in Semiconductor				
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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App.#	Title:	inventor(s)	Filing Daté	Mew:Attorney Docket:No:	Former Attorney Docket No.
	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
Į.	Methods for the Deposition of Silver				_
	and Silver Oxide Films and Patterned				
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
404400 070	Semiconductor Process Residue		00/00/000		
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	0217 150 000
00/409,020	Carbon bloxide	ruly, et al.	03/13/2003	60937-130-PK	8317-150-888
]	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing			·	
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
	3				
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of				
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
10/404 405	Chemical Mechanical Polishing	Omall at al	02/07/0002	00007 474 110	0047 474 000
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid Compositions for Cleaning				ŧ
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
10/000,300	Load Lock System for Supercritical	Daviot, et al.	10/21/2003	00937-172-03	0517-172-999
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
	Automated Dense Phase Fluid			00001 170 00	0011 110 000
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for	···			
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
	Titanium Carboxylate Films for Use in				
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
3	Remover Formulation Containing				
60/400 700	Fluoride for Use During	1 lines	04/40/0000	00007 405 55	0047 405 000
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
1	Cleaning Composition for Removing Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	9317 100 000
00/404,125	Deposition of Permanent Polymer	nii abawa, et al.	04/21/2003	00937-100-PK	8317-186-888
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999
		rtoman, et al.	0 112012000	30001-101-00	0011-101-000

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	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of		!		
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				
-	Titanium, Polysilicon, and Other				
40/000 000	Substrates Using Organosulfonic	0	40/02/0002	00007 000 110	0047 000 000
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for				
60/404 054	Polishing Nobel Metal/High K Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
60/494,954	Cerium Oxide Abrasives for Chemical	Robert J. Smail	00/14/2003	60937-203-PR	0317-203-000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
00/309,920	Wechanical Folishing	Nobell 3. Official	10/10/2003	00937-204-FTX	0317-204-000
	Chemical Mechanical Polishing			'	
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
	Periodic Acid Compositions for				
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
40/005 447	Mechanical Planarization of Tantalum	0	00/00/0000	00007 045 110	0247 045 000
10/665,417	and Tantalum Nitride  Alumina Abrasive for Chemical	Small, et al.	09/22/2003	60937-215-US	8317-215-999
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
00/320,107	Particulate or Particle-Bound	Chelle, et al.	12/02/2003	00937-210-PK	0317-210-000
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
00/000,022	Particulate or Particle-Bound	Oman, et al.	10/10/2000	00337-217-110	0017-217-000
10/690,626	i e	Small, et al.	10/23/2003	60937-217-US	8317-217-999
10.000,020	Chemical Mechanical Polishing of STI			0000. 211 00	
1	Features on Semiconductors: Water			,	
60/533,054	1	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
10/25 / 55	Method and Apparatus for Substrate				;
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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App.#	Title is	###_!Iñventor(s)a	Filling Date	New Attorney Docket No.	Former Attorney Docket No
	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888

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